Dual P-Ch MOSFET

General Description

The WSD2075DN is the highest performance trench Dual P-ch MOSFETs with extreme high cell density , which provide excellent RDSON and gate charge for most of the synchronous buck converter applications .

The WSD2075DN meet the RoHS and Green Product requirement 100% EAS guaranteed with full function reliability approved.

Features

- Advanced high cell density Trench technology
- Super Low Gate Charge
- Excellent CdV/dt effect decline
- 100% EAS Guaranteed
- Green Device Available

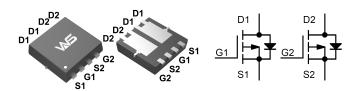
Product Summery

BVDSS	RDSON	ID
-20V	$9.5 m\Omega$	-36A

Applications

- High Frequency Point-of-Load Synchronous Buck Converter for MB/NB/UMPC/VGA
- Networking DC-DC Power System
- Load Switch

DFN3x3A-8_EP Pin Configuration



Absolute Maximum Ratings @T_A=25 ℃ unless otherwise noted

Symbol	Parameter		Ratings	Unit	
Voss	Drain-Source Voltage		-20	V	
Vgss	Gate-Source Voltage		±12	V	
lo	Drain Current (Continuous) *AC	Tc=25°C	-36	А	
	Diam Current (Continuous) AC	Tc=100°C	-23	А	
Ідм	Drain Current (Pulse) *B		-108	А	
Pb	Power Dissipation	Tc=25°C	23	W	
Т./Тѕтс	Operating Temperature/ Storage Temperature		-55~150	$^{\circ}$	
RthJC	Maximum Junction-to-Ambient		5.4	°C/W	



Electrical Characteristics @T_A=25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Тур	Max	Unit			
Static									
V(BR)DSS	Drain-Source Breakdown Voltage	Vgs = 0V, Ip= -250µA	-20			V			
IDSS	Zero Gate Voltage Drain Current	V _{DS} = -20V, V _{GS} = 0V			-1	μΑ			
V _{GS(TH)}	Gate Threshold Voltage	Vgs = Vps, Ips= 250µA	-0.4	-0.8	-1.2	V			
lgss	Gate Leakage Current	V _{GS} = ±12V, V _{DS} =0V			±100	nA			
RDS(on)	Drain-Source On-state Resistance	V _G S = -10V, I _D = -6A		9.5	12	mΩ			
		Vgs = -4.5V, ID = -6A		11	14	mΩ			
		V _{GS} = -2.5V, I _D = -4A		14	18	mΩ			
VsD	Diode Forward Voltage	IsD= -1A , Vgs=0V		-0.73	-1.2	V			
Is	Diode Forward Current *AC	Tc =25°C			-19	Α			
Switching									
Qg	Total Gate Charge			28		nC			
Qgs	Gate-Source Charge	VDS = -10V, VGS = - 4.5V, ID = -9.5A		3.5		nC			
Qgd	Gate-Drain Charge			5.6		nC			
td (on)	Turn-on Delay Time	VDD = -10V, RL = 1.3Ω ID ≅ -7.6A, VGEN = - 4.5V, Rg = 1Ω		30		ns			
tr	Turn-on Rise Time			54		ns			
td(off)	Turn-off Delay Time			135		ns			
tf	Turn-Off Fall Time			63		ns			
Dynamic					_				
Ciss	Input Capacitance	VDS = -10V, VGS = 0 V, f = 1 MHz		2565		pF			
Coss	Output Capacitance			260		pF			
Crss	Reverse Transfer Capacitance			240		pF			

A: The value of ReJA is measured with the device mounted on 1in₂ FR-4 board with 2oz. Copper, in a still air environment with TA=25°C.

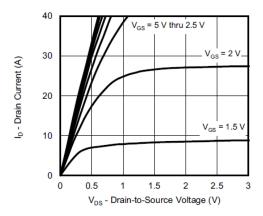
The value in any given application depends on the user's specific board design.

B: Repetitive rating, pulse width limited by junction temperature.

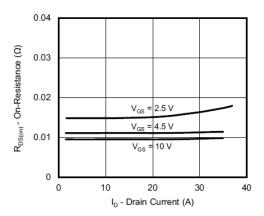
C: The current rating is based on the $t \le 10s$ junction to ambient thermal resistance rating, Wire Bond Limited 10A.



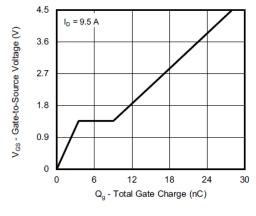
Typical Characteristics



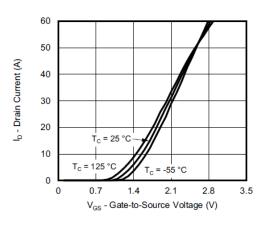
Output Characteristics



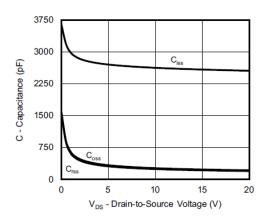
On-Resistance vs. Drain Current and Gate Voltage



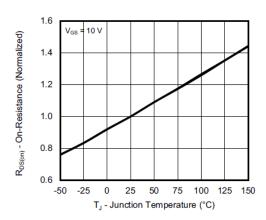
Gate Charge



Transfer Characteristics



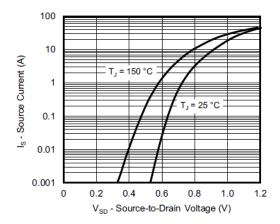
Capacitance



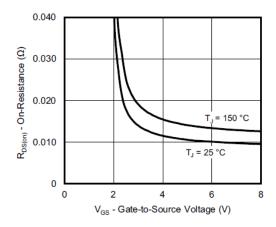
On-Resistance vs. Junction Temperature



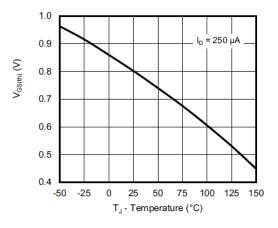
Typical Characteristics



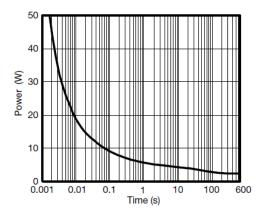
Source-Drain Diode Forward Voltage



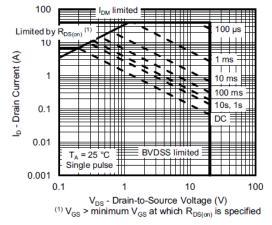
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage



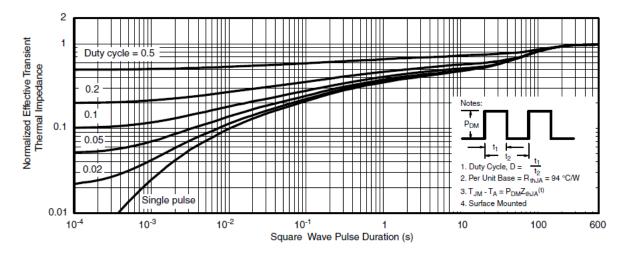
Single Pulse Power, Junction-to-Ambient



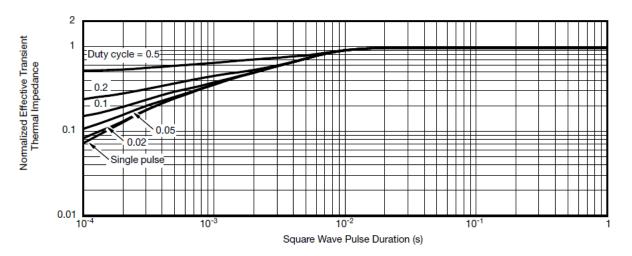
Safe Operating Area, Junction-to-Ambient



Typical Characteristics



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Case



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